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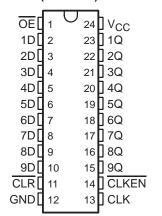
- State-of-the-Art EPIC-IIB™ BiCMOS Design Significantly Reduces Power Dissipation
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17
- Typical V_{OLP} (Output Ground Bounce) < 1 V at V_{CC} = 5 V, T_A = 25°C
- High-Impedance State During Power Up and Power Down
- High-Drive Outputs (-32-mA I_{OH}, 64-mA I_{OL})
- Buffered Control Inputs to Reduce dc Loading Effects
- Package Options Include Plastic Small-Outline (DW) and Shrink Small-Outline (DB) Packages, Ceramic Chip Carriers (FK) and Flatpacks (W), and Standard Plastic (NT) and Ceramic (JT) DIPs

description

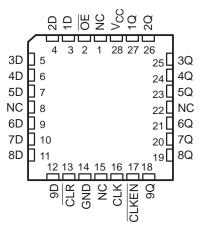
These 9-bit flip-flops feature 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing wider buffer registers, I/O ports, bidirectional bus drivers with parity, and working registers.

With the clock-enable (CLKEN) input low, the nine D-type edge-triggered flip-flops enter data on the low-to-high transitions of the clock. Taking CLKEN high disables the clock buffer, thus latching the outputs. Taking the clear (CLR) input low causes the nine Q outputs to go low, independently of the clock.

SN54ABT823 . . . JT OR W PACKAGE SN74ABT823 . . . DB, DW, OR NT PACKAGE (TOP VIEW)



SN54ABT823 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

A buffered output-enable (\overline{OE}) input can be used to place the nine outputs in either a normal logic state (high or low logic level) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54ABT823 is characterized for operation over the full military temperature range of -55° C to 125° C. The SN74ABT823 is characterized for operation from -40° C to 85° C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

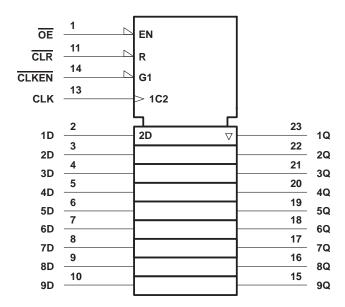
EPIC-IIB is a trademark of Texas Instruments Incorporated.



FUNCTION TABLE (each flip-flop)

	OUTPUT				
OE	CLR	CLKEN	CLK	D	Q
L	L	Х	Χ	Χ	L
L	Н	L	\uparrow	Н	Н
L	Н	L	\uparrow	L	L
L	Н	Н	Χ	Χ	Q ₀
Н	X	Χ	X	X	Z

logic symbol†

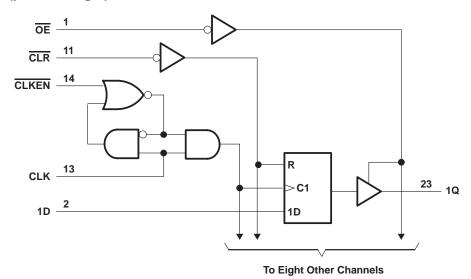


[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the DB, DW, JT, NT, and W packages.



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logic diagram (positive logic)



Pin numbers shown are for the DB, DW, JT, NT, and W packages.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	–0.5 V to 7 V
Input voltage range, V _I (see Note 1)	0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, VO	
Current into any output in the low state, IO: SN54ABT823	96 mA
SN74ABT823	128 mA
Input clamp current, I _{IK} (V _I < 0)	–18 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ_{JA} (see Note 2): DB package	104°C/W
DW package	81°C/W
NT package	67°C/W
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond those indicated in the "recommended operating conditions" section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



^{2.} The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for through-hole packages, which use a trace length of zero.

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recommended operating conditions (see Note 3)

		SN54ABT823		SN74A	UNIT	
		MIN	MAX	MIN	MAX	UNII
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2		2		V
V _{IL}	Low-level input voltage		0.8		0.8	V
VI	Input voltage	0	VCC	0	VCC	V
loн	High-level output current		-24		-32	mA
loL	Low-level output current		48		64	mA
Δt/Δν	Input transition rise or fall rate		5		5	ns/V
Δt/ΔV _{CC}	Power-up ramp rate	200		200		μs/V
TA	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		Т	A = 25°C	;	SN54A	BT823	SN74ABT823		UNIT	
PARAMETER			MIN	TYP [†]	MAX	MIN	MAX	MIN	MAX	UNIT	
VIK	V _{CC} = 4.5 V,	I _I = -18 mA			-1.2		-1.2		-1.2	V	
	V _{CC} = 4.5 V,	$I_{OH} = -3 \text{ mA}$	2.5			2.5		2.5			
\/a	V _{CC} = 5 V,	I _{OH} = -3 mA	3			3		3		V	
VOH	V00 - 45 V	$I_{OH} = -24 \text{ mA}$	2			2				V	
	V _{CC} = 4.5 V	$I_{OH} = -32 \text{ mA}$	2*					2	MAX		
Va	V00 - 45 V	I _{OL} = 48 mA			0.55		0.55			V	
VOL	V _{CC} = 4.5 V	I _{OL} = 64 mA			0.55*				0.55	V	
V _{hys}				100						mV	
lį	V _{CC} = 5.5 V,	V _I = V _{CC} or GND			±1		±1		±1	μА	
lozpu [‡]	$V_{CC} = 0 \text{ to } 2.1 \text{ V}, V_{O} = 0.5 \text{ V to } 2.7 \text{ V}, \overline{OE} = X$				±50		±50		±50	μА	
I _{OZPD} ‡	$V_{CC} = 2.1 \text{ V to } 0, V_{O} = 0.5 \text{ V to } 2.7 \text{ V}, \overline{OE} = X$				±50		±50		±50	μА	
lozh	$V_{CC} = 2.1 \text{ V to } 5.5 \text{ V}, V_{O} = 2.7 \text{ V}, \overline{OE} \ge 2 \text{ V}$				10§		10§		10§	μА	
l _{OZL}	$V_{CC} = 2.1 \text{ V to } 5.5 \text{ V, V}_{O} =$	= 0.5 V, OE ≥ 2 V			-10§		-10§		-10§	μΑ	
l _{off}	$V_{CC} = 0$,	V_I or $V_O \le 4.5 \text{ V}$			±100				±100	μА	
ICEX	V _{CC} = 5.5 V, V _O = 5.5 V	Outputs high			50		50		50	μА	
IO¶	V _{CC} = 5.5 V,	V _O = 2.5 V	-50	-140	-180	-50	-180	-50	-180	mA	
		Outputs high		1	250		250		250	μА	
ICC	$V_{CC} = 5.5 \text{ V}, I_{O} = 0,$ $V_{I} = V_{CC} \text{ or GND}$	Outputs low		24	38		38		38	mA	
	11-100000000	Outputs disabled		0.5	250		250		250	μΑ	
Δl _{CC} #	V _{CC} = 5.5 V, One input at Other inputs at V _{CC} or GN				1.5		1.5		1.5	mA	
C _i	V _I = 2.5 V or 0.5 V			4						pF	
Co	V _O = 2.5 V or 0.5 V			7						pF	

^{*} On products compliant to MIL-PRF-38535, this parameter does not apply.

[#]This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.



[†] All typical values are at $V_{CC} = 5 \text{ V}$.

[†] This parameter is characterized, but not production tested.

[§] This data sheet limit may vary among suppliers.

[¶] Not more than one output should be tested at a time, and the duration of the test should not exceed one second.

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timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

			V _{CC} = 5 V, T _A = 25°C		SN54ABT823		SN74ABT823		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
fclock	Clock frequency		0	125	0	125	0	125	MHz
	Pulse duration	CLR low	5.5		5.5		5.5		ns
t _W		CLK high	2.9		2.9		2.9		
		CLK low	3.8		3.8		3.8		
		CLR inactive	2.5		2.5		2.5		
١.	Setup time before CLK↑	Data 2.1	2.1		2.1		2.1		ns
t _{su}	Setup time before CEKT	CLKEN high	2	. 2		2] "	
		CLKEN low	3.3		3.3		3.3		
th	Hold time after CLK↑	Data	1.3		1.3		1.3		
		CLKEN high	1		1		1		ns
		CLKEN low	2		2		2		

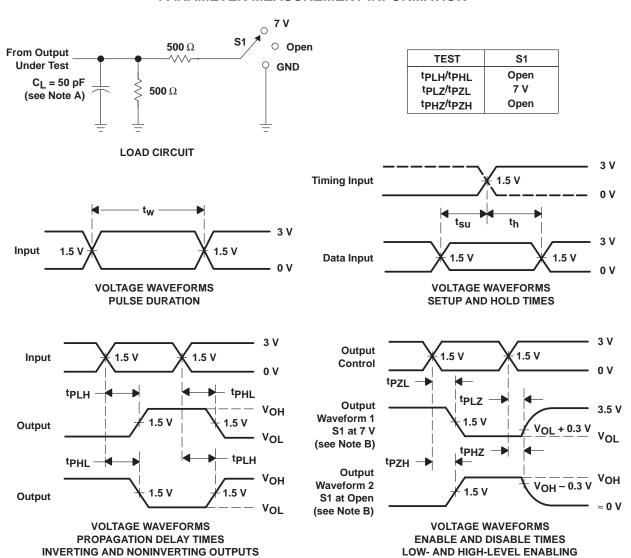
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V ₍	CC = 5 V 4 = 25°C	', ;	SN54A	BT823	SN74A	BT823	UNIT
	(INFOT)	(0011-01)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f _{max}			125	200		125		125		MHz
t _{PLH}	CLK	Q	2.1	4.3	5.9	2.1	8.1	2.1	6.8	ns
t _{PHL}		Q	2.2	4.4	6.1	2.2	7	2.2	6.7	115
t _{PHL}	CLR	Q	2	4.1	6.3	2	7.3	2	7.1	ns
^t PZH		Q	1	3	4.7†	1	6.3	1	6†	no
t _{PZL}	ŌĒ	Q	2.2	4.1	5.6	2.2	6.6	2.2	6.5†	ns
^t PHZ	ŌĒ	Q	2.7	4.8	6.5†	2.7	7.7	2.7	7.5†	ns
t _{PLZ}	OE	α	1.9	5	6.4	1.9	7.4	1.9	6.9	115

[†] This data sheet limit may vary among suppliers.

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns. $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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